

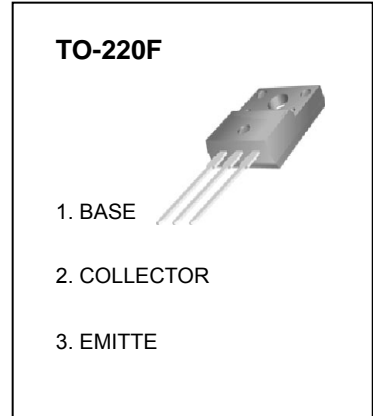
## 3DA5371 TRANSISTOR (NPN)

### FEATURES

- Breakdown Voltage High
- Reverse Cut-off Current Small
- Saturation Voltage Low
- Power dissipation

$P_{CM} : 1.5W (T_{amb}=25^{\circ}C)$

$25 W (T_{case}=25^{\circ}C)$



### MAXIMUM RATINGS ( $T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	180	V
$V_{CEO}$	Collector-Emitter Voltage	160	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current -Continuous	1.5	A
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature	-55-150	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=180V, I_E=0$			10	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=6V, I_C=0$			10	$\mu A$
DC current gain	$h_{FE}^*$	$V_{CE}=5V, I_C=200mA$	60		240	
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=500mA, I_B=50mA$			1	V
Transition frequency	$f_T$	$V_{CE}=10V, I_C=50mA$	50			MHz

\*Pulse test:  $t_p \leq 300\mu S, \delta \leq 0.02$ .

### CLASSIFICATION OF $h_{FE}$

Rank	O	R
Range	60-140	100-240

# Typical Characteristics

3DA5371

